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Understanding the interfacial growth mechanism is essential for controlling the film morphology and properties. However, a straightforward picture of the growth mode under different growth conditions is still lacking. In this talk, I will introduce a comprehensive interfacial growth theory based on the stochastic approach. Using a critical interisland separation, we construct a general phase diagram of the growth modes. Both first-principle calculations and experiments with zinc oxide growth by chemical vapor deposition have been utilized to demonstrate the theoretical model. Besides, I will also introduce our systematic work about the influence of the strain on the growth structure and defects formation.

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邀请人:

xzli@pku.edu.cn

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